

OCT 21 2005

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Reply to the Office Action dated 10/04/2005

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AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at Page 9, Line 17 with the following rewritten paragraph (showing changes):

There are many options for the order sequence of the steps for forming the LDD, S/D, Halo, threshold voltage I/I and doped depletion regions. Furthermore, the process can include steps to dope the upper portion of the substrate (e.g., first doped region 131), especially in the area between the S/D 150 and doped depleted regions 130. For example, field implants, Vt implants, halo implants can be performed to dope the first doped region 131. ~~These~~ The order of these ~~step- steps~~ is only limited by feasibility.

Please replace the paragraph beginning at Page 12, Line 4 with the following rewritten paragraph (showing changes):

Isolation regions 102, as shown in figure ~~1~~ 3A, can be formed at any point in the process. Isolation regions 102 are preferably shallow trench isolation (STI) regions.

Please replace the paragraph beginning at Page 14, Line 9 with the following rewritten paragraph (showing changes):

Preferably the doped depletion region has ~~an~~ a second type impurity concentration slightly higher than the total first conductivity type dopants in the substrate between the doped depletion regions 130 and S/D regions 150 or (first impurity doped

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1 region 131). Preferably the doped depletion regions 130 have an impurity concentration
2 high enough to counter act the opposite impurity concentration in the substrate so that a
3 portion of the lightly doped depletion region 130 has effectively a net impurity
4 concentration between $1E16$ and $5E18$ atoms/cc. This portion of the doped depletion
5 region is electrically effectively an insulator (like a dielectric layer).

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